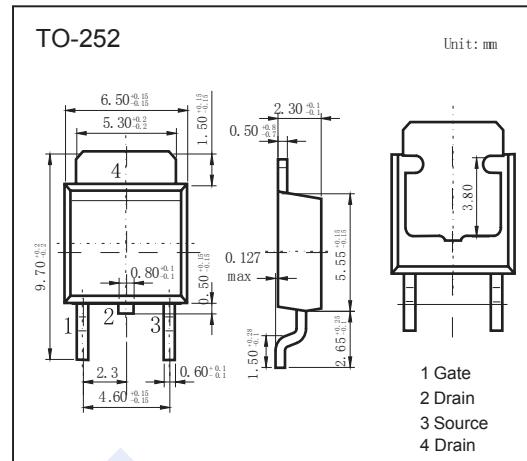
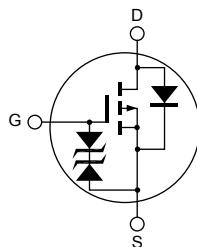


P-Channel MOSFET

2SJ506S

■ Features

- $V_{DS} (V) = -30V$
- $I_D = -10 A$
- $R_{DS(ON)} < 85m\Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 180 \Omega$ ($V_{GS} = -4V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	-10	A
Pulsed Drain Current (Note.1)	I_{DM}	-40	
Body to Drain Diode Reverse Drain Current	I_{DR}	-10	
Power Dissipation	P_D	20	W
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: PW ≤ 10 us, duty cycle $\leq 1\%$

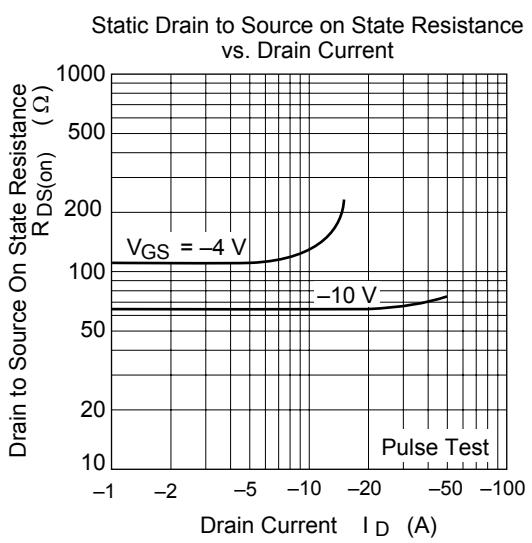
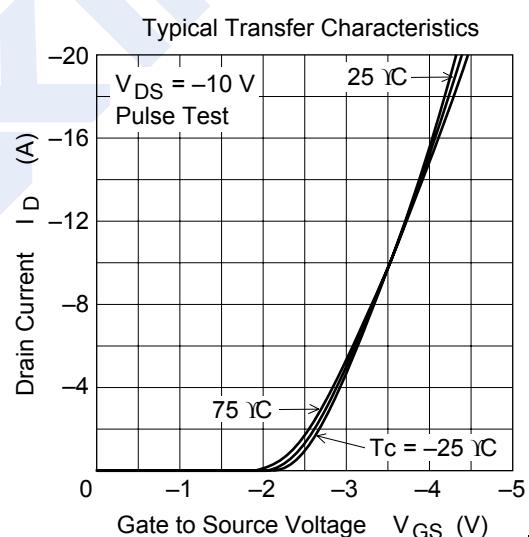
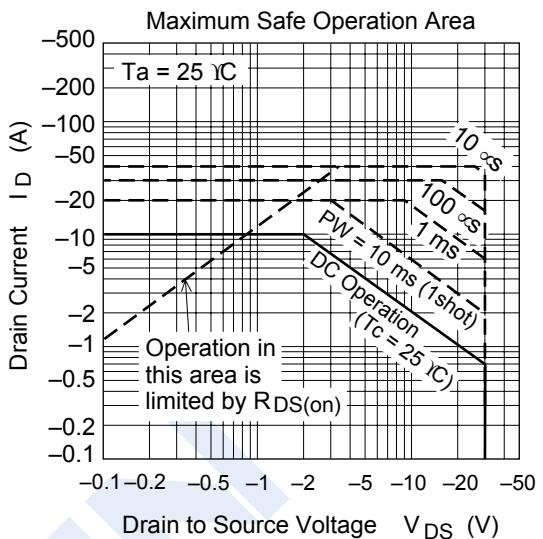
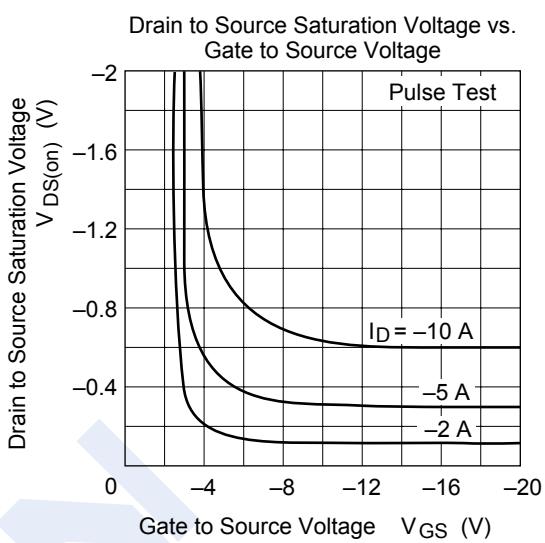
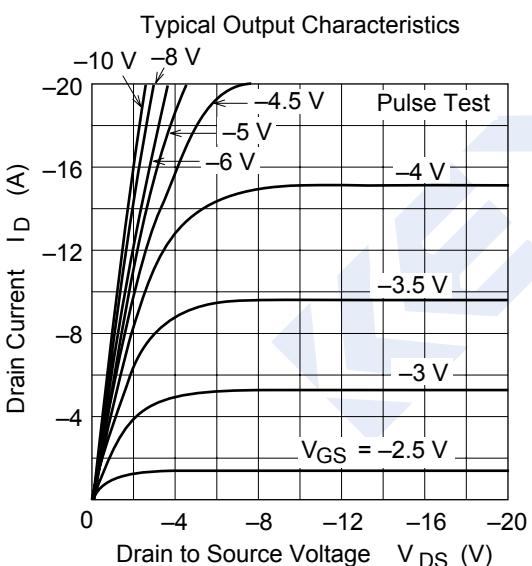
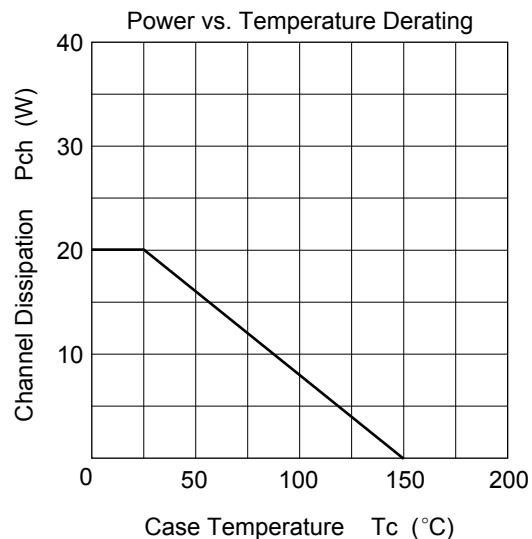
■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -10mA, V_{GS} = 0V$	-30			V
Gate-Source Breakdown Voltage	V_{GSS}		± 20			
Zero Gate Voltage Drain Current	I_{BS}	$V_{DS} = -30V, V_{GS} = 0V$			-10	uA
Gate-Body leakage current	I_{GS}				± 10	uA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -10V, I_D = -1mA$	-1		-2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -5A$			85	$m\Omega$
		$V_{GS} = -4V, I_D = -5A$			180	
Forward Transconductance	g_{FS}	$V_{DS} = -10V, I_D = -5A$	10	16		S
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$			660	pF
Output Capacitance	C_{oss}				440	
Reverse Transfer Capacitance	C_{rss}				140	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -10V, I_D = -5A, R_L = 2\Omega$			12	ns
Turn-On Rise Time	t_r				65	
Turn-Off Delay Time	$t_{d(off)}$				85	
Turn-Off Fall Time	t_f				65	
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -10A, dI/dt = 50A/\mu s, V_{GS} = 0$			65	
Diode Forward Voltage	V_{SD}	$I_S = -10A, V_{GS} = 0V$			-1.05	V

P-Channel MOSFET

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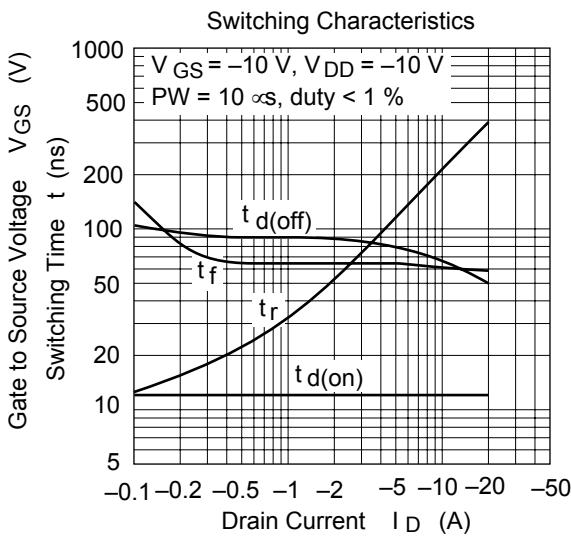
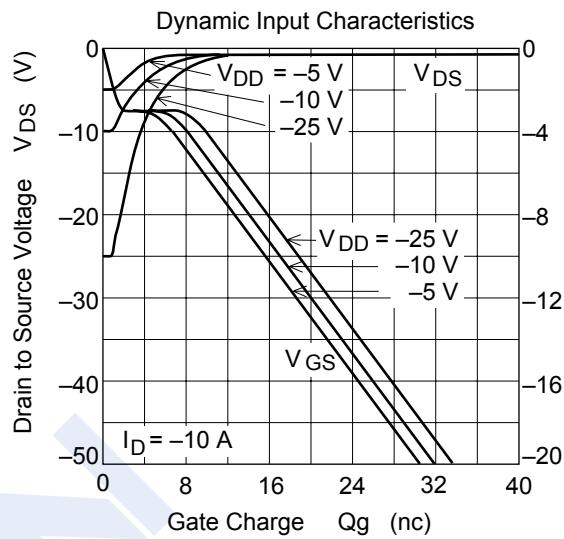
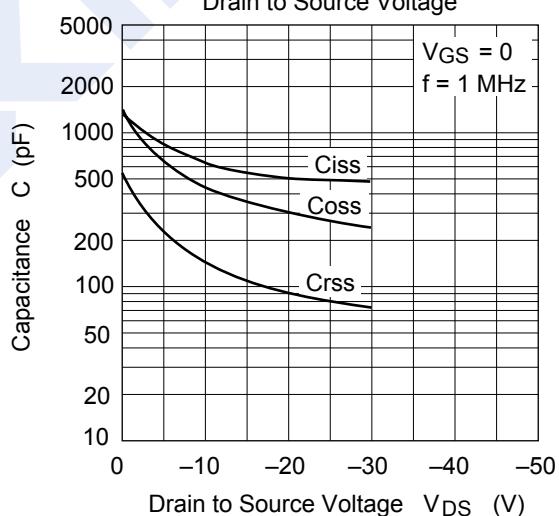
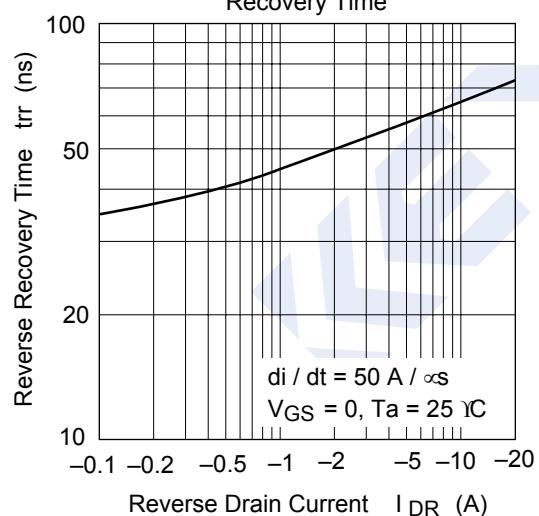
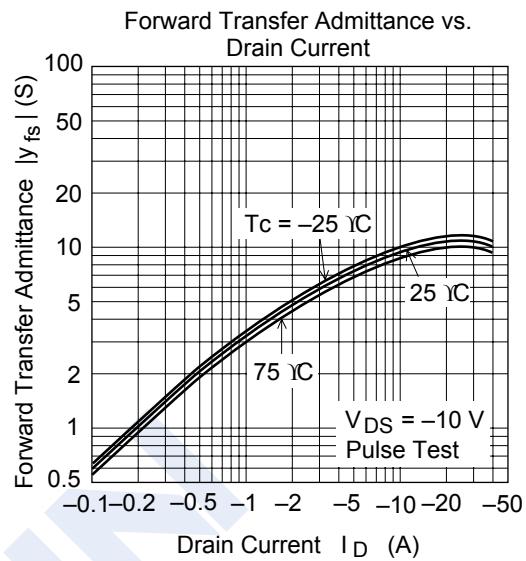
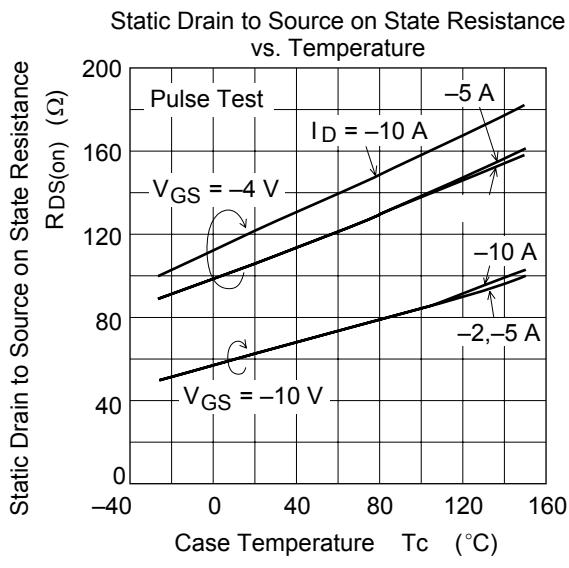
■ Typical Characteristics



P-Channel MOSFET

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■ Typical Characteristics



P-Channel MOSFET

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■ Typical Characteristics

